



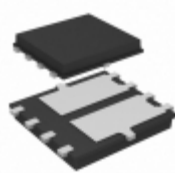
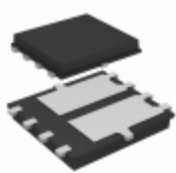
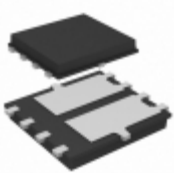

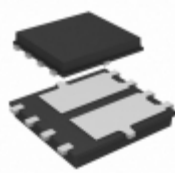
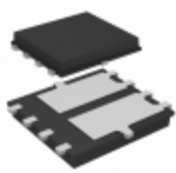
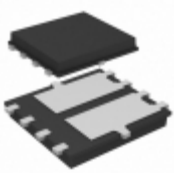
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|---|---|
|  | <h2>SI7904BDN-T1-GE3</h2> |
| | <p>Hersteller-Teilenummer: SI7904BDN-T1-GE3</p> <p>Hersteller / Marke: Electro-Films (EFI) / Vishay</p> <p>Teil der Beschreibung: MOSFET 2N-CH 20V 6A PPAK 1212-8</p> <p>Datenblätter:  SI7904BDN-T1-GE3.pdf</p> <p>RoHs Status: Bleifrei / RoHS-konform</p> <p>Lagerzustand: New original, 201500 pcs Stock Available.</p> <p>Liefern von: Hong Kong</p> <p>Versandweg: DHL/Fedex/TNT/UPS/EMS</p> |
| <p>Image may be representation. See specs for product details.</p> | |

Spezifikationen

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|--|---|
| Teilenummer | SI7904BDN-T1-GE3 |
| Hersteller | Electro-Films (EFI) / Vishay |
| Beschreibung | MOSFET 2N-CH 20V 6A PPAK 1212-8 |
| Kategorie | Diskrete Halbleiterprodukte > Transistoren-FETs, |
| Teilstatus | 201500 pcs Stock |
| Hersteller Standard Vorlaufzeit | 33 Weeks |
| detaillierte Beschreibung | Mosfet Array 2 N-Channel (Dual) 20V 6A 17.8W |
| Serie | TrenchFET® |
| Betriebstemperatur | -55°C ~ 150°C (TJ) |
| Befestigungsart | Surface Mount |
| Leistung - max | 17.8W |
| Verpackung / Gehäuse | PowerPAK® 1212-8 Dual |
| Supplier Device-Gehäuse | PowerPAK® 1212-8 Dual |
| Typ FET | 2 N-Channel (Dual) |
| FET-Merkmal | Logic Level Gate |
| Drain-Source-Spannung (Vdss) | 20V |
| Strom - Ununterbrochener Abfluss (Id) bei 25 ° C | 6A |
| Rds On (Max) @ Id, Vgs | 30 mOhm @ 7.1A, 4.5V |
| VGS (th) (Max) @ Id | 1V @ 250µA |
| Gate Charge (Qg) (Max) @ Vgs | 24nC @ 8V |
| Eingabekapazität (Ciss) (Max) @ Vds | 860pF @ 10V |
| Verpackung | Tape & Reel (TR) |
| Basisteilenummer | SI7904 |
| Bleifreier Status / RoHS-Status | Lead free / RoHS Compliant |
| Feuchtigkeitsempfindlichkeitsniveau (MSL) | 1 (Unlimited) |
| Andere Namen | SI7904BDN-T1-GE3-ND |

SI7904BDN-T1-GE3 ist neu im Original, Suche SI7904BDN-T1-GE3 Datenblätter, PDF, Inventar bei Y-IC.com Online, Bestellen Sie SI7904BDN-T1-GE3 Electro-Films (EFI) / Vishay mit Garantie und Vertrauen. Anfrage SI7904BDN-T1-GE3: Info@Y-IC.com

Sie können auch interessiert sein:

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|---|---|---|---|
|  <p>SI7904DN-T1 VISHAY SI7904DN-T1 VISHAY</p> |  <p>SI7904DN-T1-GE3 Electro-Films (EFI) / Vishay MOSFET 2N-CH 20V 5.3A 1212-8</p> |  <p>SI7904BDN-T1-GE3 Vishay / Siliconix MOSFET 2N-CH 20V 6A PPAK 1212-8</p> |  <p>SI7904BDN-T1-E3 Vishay / Siliconix MOSFET 2N-CH 20V 6A 1212-8</p> |
|  <p>SI7904DN V SI7904DN V</p> |  <p>SI7904DN-T1-E3 Vishay / Siliconix MOSFET 2N-CH 20V 5.3A 1212-8</p> |  <p>SI7904DN-T1-E3 Electro-Films (EFI) / Vishay MOSFET 2N-CH 20V 5.3A 1212-8</p> |  <p>SI7904BDN-T1-E3 Electro-Films (EFI) / Vishay MOSFET 2N-CH 20V 6A 1212-8</p> |

heiße Teile

Mehr

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| <ul style="list-style-type: none"> SI7892DP SI7898DP-T1-E3 SI7900AEDN SI7900AEDN-T1-GE3 SI7901EDN-T1 SI7904BDN-T1-GE3 SI7904DN-T1-GE3 SI7909DN-T1-E3 SI7911DN-T1-E3 SI7913DN-T1-GE3 | <ul style="list-style-type: none"> SI7892DP-T1 SI7898DP-T1-E3 SI7900AEDN-T1 SI7900EDN SI7901EDN-T1-E3 SI7904DN SI7904DN-T1-GE3 SI7909DN-T1-GE3 SI7911DN-T1-GE3 SI7913DN-T1-GE3 | <ul style="list-style-type: none"> SI7892DP-T1-E3 SI7898DP-T1-GE3 SI7900AEDN-T1-E3 SI7900EDN-T1 SI7901EDN-T1-E3 SI7904DN-T1 SI7905DN-T1-GE3 SI7909DN-T1-GE3 SI7911DN-T1-GE3 SI7922DN-T1-E3 | <ul style="list-style-type: none"> SI7892DP-T1-GE3 SI7898DP-T1-GE3 SI7900AEDN-T1-E3 SI7900EDN-T1-E3 SI7904BDN-T1-E3 SI7904DN-T1-E3 SI7905DN-T1-GE3 SI7911DN SI7913DN-T1-E3 SI7922DN-T1-E3 | <ul style="list-style-type: none"> SI7898DP SI7900ADN SI7900AEDN-T1-GE3 SI7900EDN-T1-GE3 SI7904BDN-T1-E3 SI7904DN-T1-E3 SI7909DN-T1-E3 SI7911DN-T1-E3 SI7913DN-T1-E3 SI7922DN-T1-GE3 |
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